

# PSMN1R2-30YLC

# N-channel 30 V 1.25m $\Omega$ logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 3 May 2011

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

## 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	215	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12		-	1.35	1.65	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u>		-	1.05	1.25	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see Figure 15	-	11.6	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	38	-	nC

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	[Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PSMN1R2-30YLC	1C230L

<sup>[1] % =</sup> placeholder for manufacturing site code

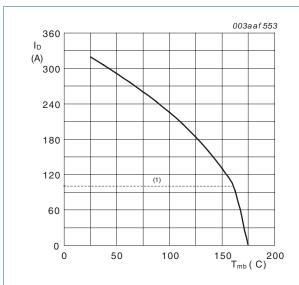
# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

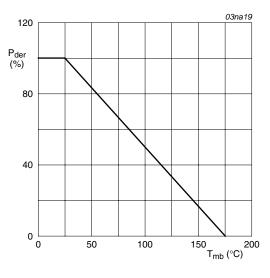
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{ or } \text{ or }  o$	<u>[1]</u> _	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; see Figure 4	-	1237	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	215	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	900	-	V
Source-drain	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	[1] -	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	1237	Α
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped; see Figure 3	-	209	mJ

<sup>[1]</sup> Continuous current is limited by package.



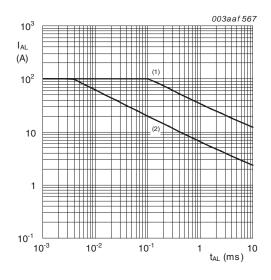
 $V_{GS} \ge 10V$ ; (1) Capped at 100A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



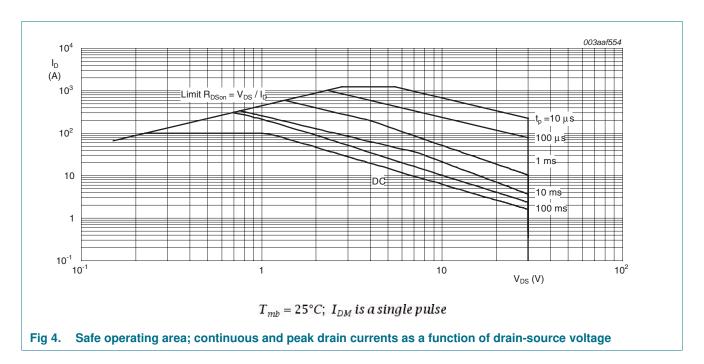
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1)  $T_{j(init)} = 25^{\circ}C$ ; (2)  $T_{j(init)} = 100^{\circ}C$ 

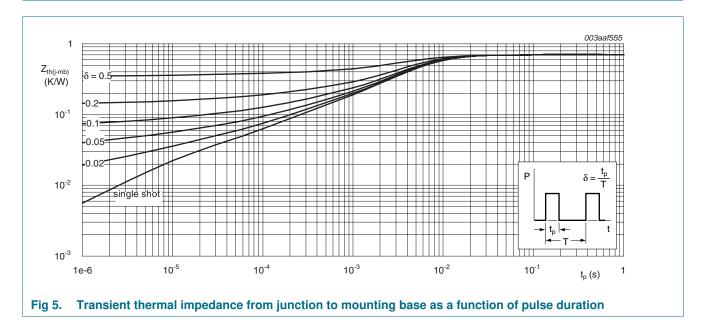
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



#### 6. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.58	0.7	K/W



# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.46	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	1.35	1.65	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	2.8	mΩ
		$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see <u>Figure 12</u>	-	1.05	1.25	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	2.05	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	1.1	2.2	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub> t	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	78	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	38	-	nC
		$I_D = 0 A$ ; $V_{DS} = 0 V$ ; $V_{GS} = 10 V$	-	75	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	10.3	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	6.7	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.6	-	nC
$Q_{GD}$	gate-drain charge		-	11.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.34	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	5093	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	977	-	pF
$C_{rss}$	reverse transfer capacitance		-	333	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	36	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	60	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	75	-	ns
	C 11 12		_	39	_	ns
t <sub>f</sub>	fall time			33	_	113

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{oss}$	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	33	-	nC
Source-drain	Source-drain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	41.5	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V	-	45	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 15 \text{ V; see } \frac{\text{Figure } 18}{\text{Figure } 18}$	-	25	-	ns
t <sub>b</sub>	reverse recovery fall time		-	16.5	-	ns

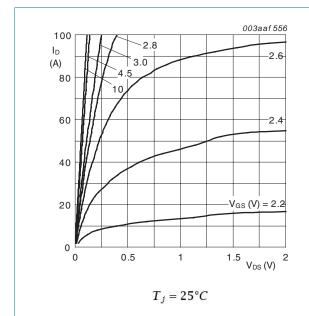


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

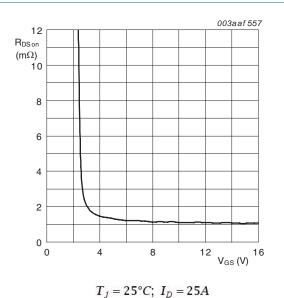
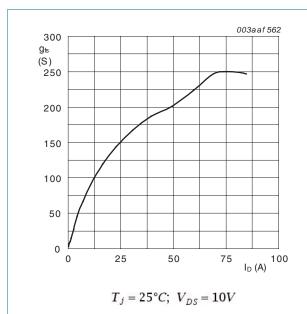


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



Forward transconductance as a function of Fig 8. drain current; typical values

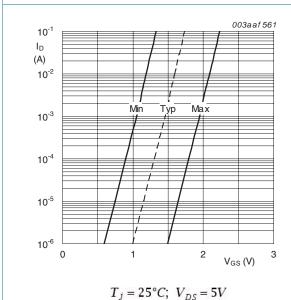
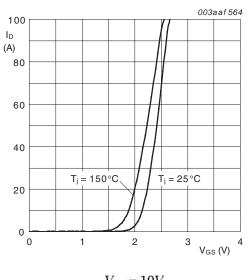


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$ 

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage

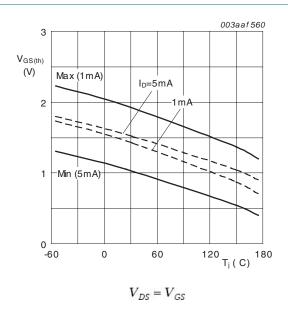


Fig 11. Gate-source threshold voltage as a function of junction temperature

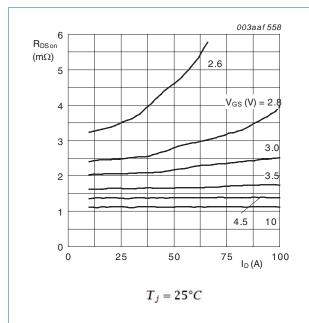


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

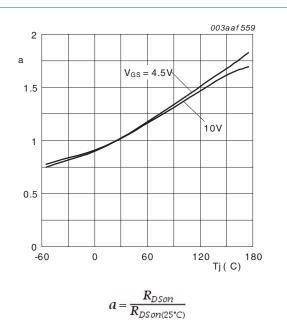


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

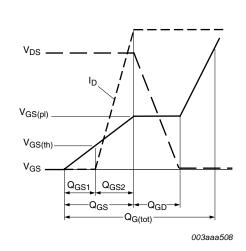


Fig 14. Gate charge waveform definitions

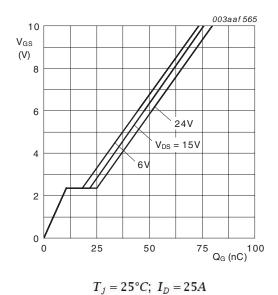


Fig 15. Gate-source voltage as a function of gate charge; typical values

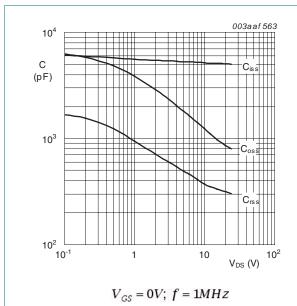


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

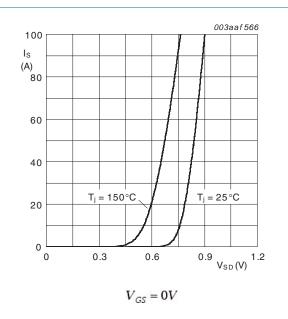


Fig 17. Source current as a function of drain-source voltage; typical values

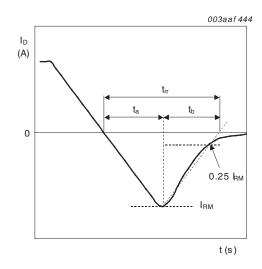


Fig 18. Reverse recovery timing definition

## Package outline

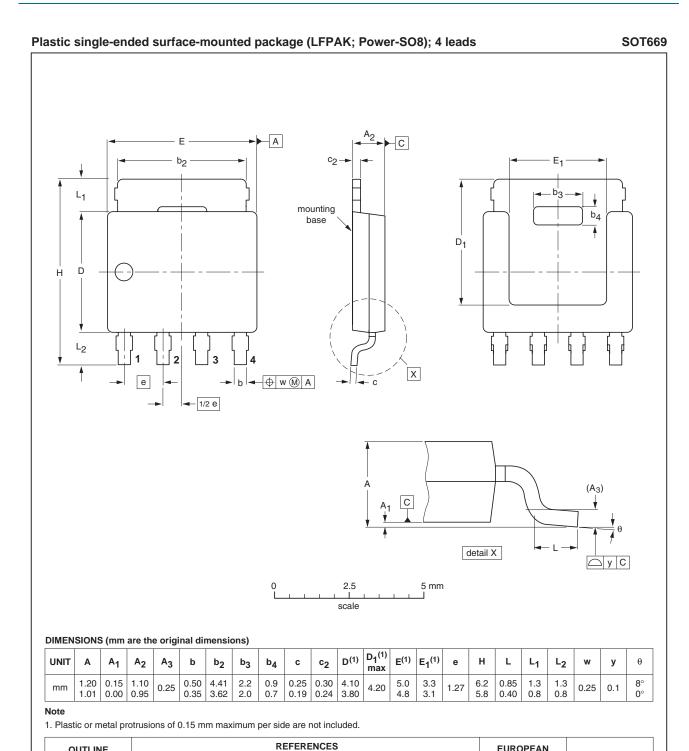


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R2-30YLC

OUTLINE

VERSION

SOT669

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**JEDEC** 

MO-235

ISSUE DATE

06-03-16

11-03-25

**EUROPEAN** 

**PROJECTION** 

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# **Revision history**

#### Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R2-30YLC v.1	20110503	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN1R2-30YLC

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# PSMN1R2-30YLC

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Product data sheet

## 12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values3
6	Thermal characteristics5
7	Characteristics6
8	Package outline
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions13
10.3	Disclaimers
10.4	Trademarks14
11	Contact information 14